

High Temperature Silicon Carbide Power Schottky Diode

V_{RRM}	=	650 V
I_F	=	2.5 A
Q_C	=	7 nC

Features

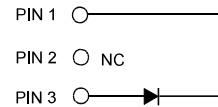
- 650 V Schottky rectifier
- 210 °C maximum operating temperature
- Electrically isolated base-plate
- Zero reverse recovery charge
- Superior surge current capability
- Positive temperature coefficient of V_F
- Temperature independent switching behavior
- Lowest figure of merit Q_C/I_F
- Available screened to Mil-PRF-19500

Advantages

- High temperature operation
- Improved circuit efficiency (Lower overall cost)
- Low switching losses
- Ease of paralleling devices without thermal runaway
- Smaller heat sink requirements
- Industry's lowest reverse recovery charge
- Industry's lowest device capacitance
- Ideal for output switching of power supplies
- Best in class reverse leakage current at operating temperature

Package

- RoHS Compliant



TO – 257 (Isolated Base-plate Hermetic Package)

Applications

- Down Hole Oil Drilling
- Geothermal Instrumentation
- Solenoid Actuators
- General Purpose High-Temperature Switching
- Amplifiers
- Solar Inverters
- Switched-Mode Power Supply (SMPS)
- Power Factor Correction (PFC)

Maximum Ratings at $T_j = 210\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values		Unit
			min.	typ.	
Repetitive peak reverse voltage	V_{RRM}			650	V
Continuous forward current	I_F	$T_C = 25\text{ °C}$		2.5	A
Continuous forward current	I_F	$T_C \leq 190\text{ °C}$		0.75	A
RMS forward current	$I_{F(RMS)}$	$T_C \leq 190\text{ °C}$		1.3	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}, t_p = 10\text{ ms}$		10	A
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25\text{ °C}, t_p = 10\text{ }\mu\text{s}$		65	A
I^2t value	$\int i^2 dt$	$T_C = 25\text{ °C}, t_p = 10\text{ ms}$		0.5	A ² S
Power dissipation	P_{tot}	$T_C = 25\text{ °C}$		24	W
Operating and storage temperature	T_j, T_{stg}			-55 to 210	°C

Electrical Characteristics at $T_j = 210\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Diode forward voltage	V_F	$I_F = 0.75\text{ A}, T_j = 25\text{ °C}$		1.4		V
		$I_F = 0.75\text{ A}, T_j = 210\text{ °C}$		2.3		
Reverse current	I_R	$V_R = 650\text{ V}, T_j = 25\text{ °C}$		1	5	μA
		$V_R = 650\text{ V}, T_j = 210\text{ °C}$		5	50	
Total capacitive charge	Q_C	$I_F \leq I_{F,MAX}$ $di_F/dt = 200\text{ A}/\mu\text{s}$ $T_j = 210\text{ °C}$	$V_R = 400\text{ V}$	7		nC
Switching time	t_s		$V_R = 400\text{ V}$	< 17		ns
Total capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}, T_j = 25\text{ °C}$		76		pF
		$V_R = 400\text{ V}, f = 1\text{ MHz}, T_j = 25\text{ °C}$		12		
		$V_R = 650\text{ V}, f = 1\text{ MHz}, T_j = 25\text{ °C}$		12		

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	9.52	°C/W
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Mechanical Properties

Mounting torque	M	0.6	Nm
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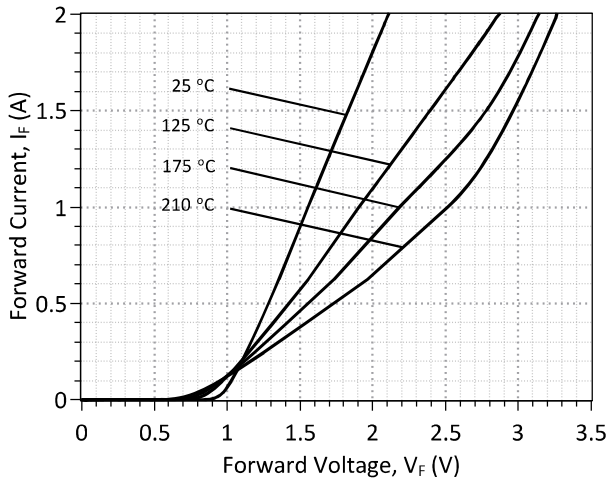


Figure 1: Typical Forward Characteristics

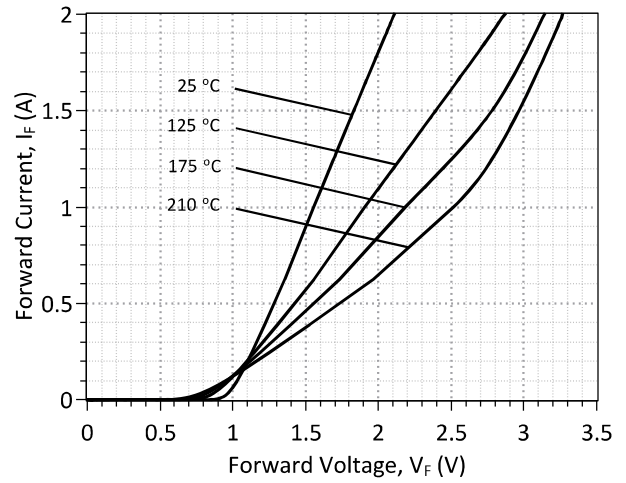


Figure 2: Typical Reverse Characteristics

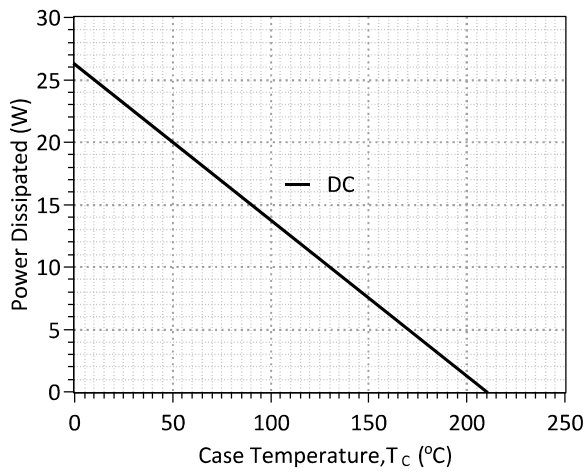


Figure 3: Power Derating Curve

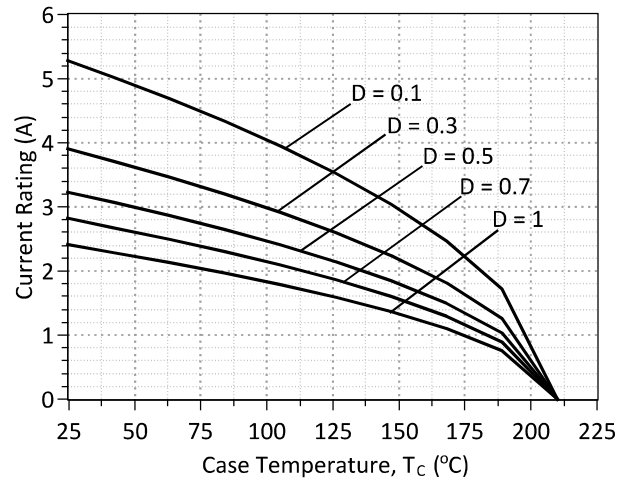


Figure 4: Current Derating Curves ($D = t_p/T$, $t_p = 400 \mu s$)
(Considering worst case Z_{th} conditions)

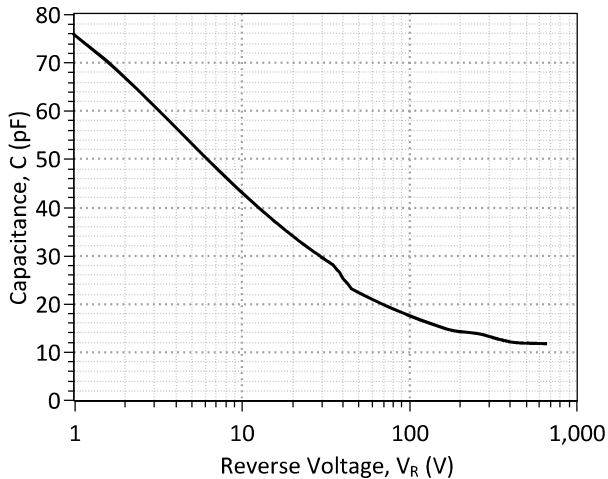


Figure 5: Typical Junction Capacitance vs Reverse Voltage

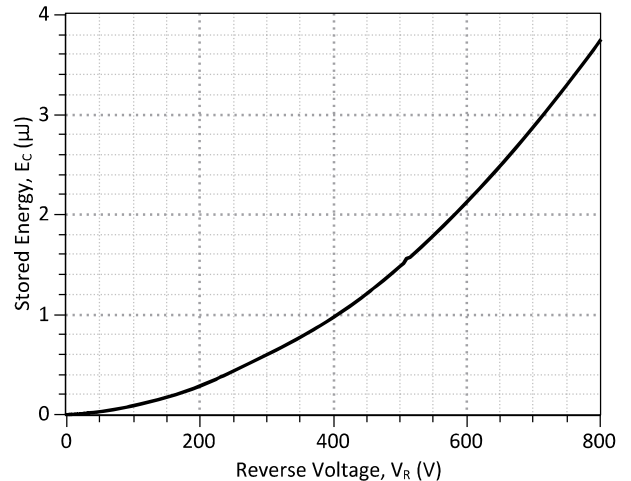


Figure 6: Typical Capacitive Energy vs Reverse Voltage

Characteristics

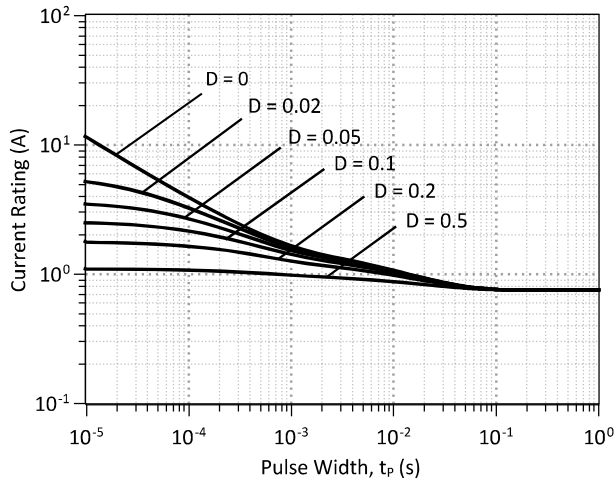


Figure 7: Current vs Pulse Duration Curves at $T_c = 190\text{ }^\circ\text{C}$

Characteristics

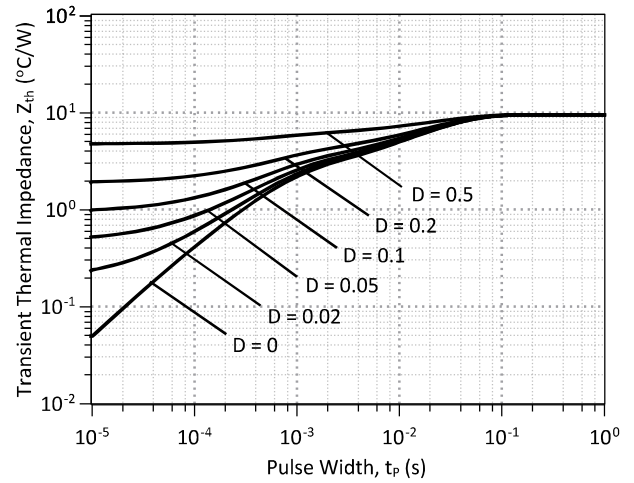
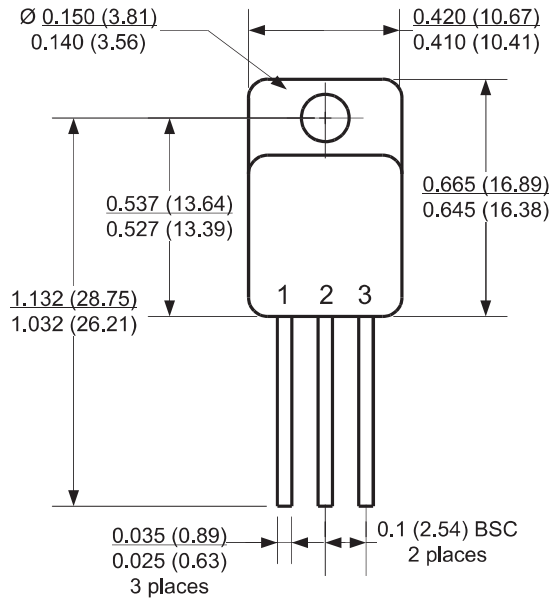


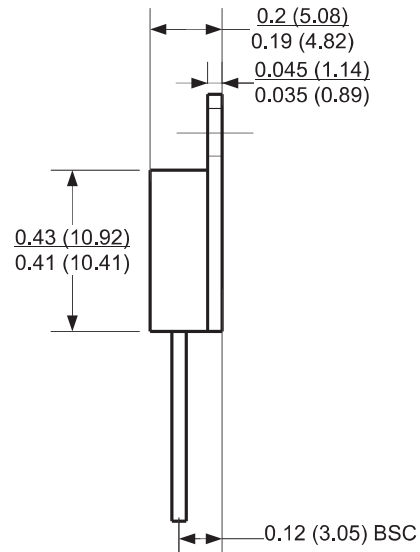
Figure 8: Transient Thermal Impedance

Package Dimensions:

TO-257



PACKAGE OUTLINE



NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History

Date	Revision	Comments	Supersedes
2014/08/26	1	Updated Electrical Characteristics	
2012/04/24	0	Initial release	

Published by

GeneSiC Semiconductor, Inc.
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Dulles, VA 20166

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SPICE Model Parameters

This is a secure document. Copy this code from the SPICE model PDF file on our website into a SPICE software program for simulation of the 1N8030-GA.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0           $
*      $Date:      05-SEP-2013   $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
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*
*      These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
*      OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
*      TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
*      PARTICULAR PURPOSE."
*      Models accurate up to 2 times rated drain current.
*
*      Start of 1N8030-GA SPICE Model
*
.SUBCKT 1N8030 ANODE KATHODE
D1 ANODE KATHODE 1N8030_25C; Call the Schottky Diode Model
D2 ANODE KATHODE 1N8030_PIN; Call the PiN Diode Model
.MODEL 1N8030_25C D
+ IS      3.57E-18          RS      0.49751
+ TRS1    0.0057           TRS2    2.40E-05
+ N       1                IKF     322
+ EG      1.2              XTI     3
+ CJO     9.12E-11         VJ      0.371817384
+ M       1.527759838     FC       0.5
+ TT      1.00E-10        BV       650
+ IBV     1.00E-03        VPK     650
+ IAVE    1                TYPE    SiC_Schottky
+ MFG     GeneSiC_Semiconductor
.MODEL 1N8030_PIN D
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+ N       5                IKF     800
+ EG      3.23             XTI     -14
+ FC      0.5              TT      0
+ BV      650              IBV     1.00E-03
+ VPK     650              IAVE    1
+ TYPE    SiC_PiN
.ENDS
*
*      End of 1N8030-GA SPICE Model
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